

PROCESS FOR FABRICATING THIN-FILM DEVICE  
AND THIN-FILM DEVICE

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ABSTRACT OF THE DISCLOSURE

10 In a process for producing a thin-film device, a  
conducting layer composed of an anodically oxidizable  
metal is formed on a substrate and is etched to form gate  
bus lines and gate electrode having upper surfaces  
parallel to the substrate and inclined side surfaces.  
The gate bus lines and the gate electrodes are anodically  
15 oxidized, so that they include inner conducting portions  
and outer insulating oxide films covering the inner  
conducting portions. The outer insulating films prevent  
the bus lines from short circuiting, and the inclined  
side surfaces of the bus lines makes it possible to  
20 fabricate a dense wiring arrangement.